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April 1st, 2010 **Renesas Electronics Corporation**

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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2SK1628, 2SK1629

Silicon N Channel MOS FET

REJ03G0960-0400 Rev.4.00 May 13, 2009

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

RENESAS Package code: PRSS0004ZF-A (Package name: TO-3PL)

1. Gate 2. Drain 3. Source

zduc

γD

4

δs

Absolute	Maximum	Ratings

				$(Ta = 25^{\circ}C)$
ltem		Symbol	Ratings	Unit
Drain to source voltage	2SK1628	V _{DSS}	450	V
	2SK1629		500	
Gate to source voltage		V _{GSS}	±30	V
Drain current		Ι _D	30	А
Drain peak current		I _{D(pulse)} * ¹	120	А
Body to drain diode reverse dr	ain current	I _{DR}	30	А
Channel dissipation		Pch* ²	200	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

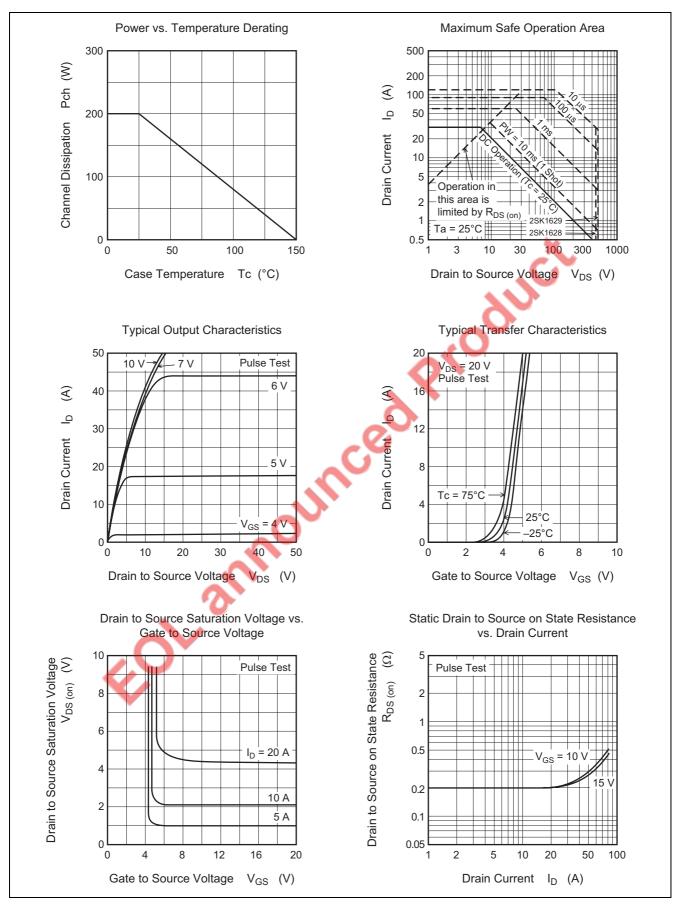
2. Value at $T_C = 25^{\circ}C$

Electrical Characteristics

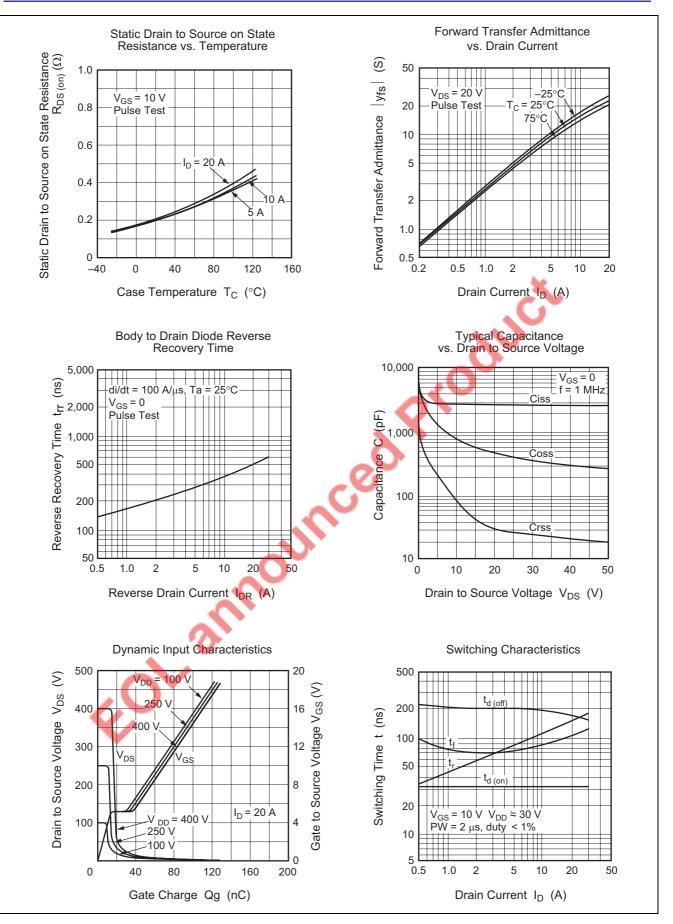
state resistance2SK16290.220.27Forward transfer admittance $ y_{fs} $ 1220S $I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$ Input capacitanceCiss2800pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitanceCoss780pFReverse transfer capacitanceCrss90pFTurn-on delay timetd(on)32nsIncert field of the strength of	$\begin{array}{c c c c c c c c c c c c c c c c c c c $
Gate to source breakdown voltage $V_{(BR)GSS}$ ± 30 $ V$ $I_G = \pm 100 \ \mu$ A, $V_{DS} = 0$ Gate to source leak current I_{GSS} $ \pm 10$ μ A $V_{GS} = \pm 25 \ V, V_{DS} = 0$ Zero gate voltage drain current $2SK1628$ I_{DSS} $ \pm 100 \ \mu$ A $V_{DS} = 360 \ V, V_{GS} = 0$ Current $2SK1629$ I_{DSS} $ 250 \ \mu$ A $V_{DS} = 360 \ V, V_{GS} = 0$ Gate to source cutoff voltage $V_{GS(off)}$ 2.0 $ 3.0$ V $I_D = 1 \ mA, V_{DS} = 10 \ V$ Static drain to source on state resistance $2SK1628 \ 2SK1629$ $R_{DS(on)}$ $ 0.20 \ 0.25 \ 0.27$ Ω $I_D = 15 \ A, V_{DS} = 10 \ V^{*3}$ Forward transfer admittance $ y_{IS} $ $12 \ 20 \ S$ $I_D = 15 \ A, V_{DS} = 10 \ V^{*3}$ Input capacitanceCiss $ 2800 \ pF$ $V_{DS} = 10 \ V, V_{GS} = 0$ Output capacitanceCoss $ 780 \ pF$ $f = 1 \ MHz$ Reverse transfer capacitanceCrss $ 90 \ pF$ $f = 1 \ MHz$ Rise time t_r $ 140 \ ns$ $I_P = 30 \ A, V_{GS} = 0$ Turn-off delay time t_f $ 100 \ ns$ $I_F = 30 \ A, V_{GS} = 0$ Body to drain diode forward voltage V_{DF} $ 1.1 \ N_S = 0$ Body to drain diode reverse recovery t_{rr} $ 600 \ ns$ </th <th>Gate to source breakdown voltage$V_{(BR)GSS}$$\pm 30VI_G = \pm 100 \ \mu$A, $V_{DS} = 0$Gate to source leak current$I_{GSS}$$\pm 10$$\muAV_{GS} = \pm 25 \ V, V_{DS} = 0$Zero gate voltage drain current$2SK1629$$I_{DSS}$$250$$\muAV_{DS} = 360 \ V, V_{GS} = 0$Gate to source cutoff voltage$2SK1629$$V_{CS}(off)$$2.0$-$3.0$$V$$I_D = 1 \ m$A, $V_{DS} = 10 \ V_{DS} = 400 \ V, V_{GS} = 0$Gate to source cutoff voltage$V_{CS}(off)$$2.0$-$3.0$$V$$I_D = 1 \ m$A, $V_{DS} = 10 \ V^3$Static drain to source on 2SK1629$2SK1629$-$0.225$$\Omega$$I_D = 15 \ A, V_{DS} = 10 \ V^3$Forward transfer admittance$y_{IS}$$12$$20$-$S$$I_D = 15 \ A, V_{DS} = 10 \ V^3$Input capacitanceCiss-$2800$-$pF$$V_{DS} = 10 \ V, V_{SS} = 0$Output capacitanceCiss-$2800$-$pF$$V_{DS} = 10 \ V, V_{SS} = 0$Reverse transfer capacitanceCiss-90-$pF$$I_T$Turn-off delay time$t_d(off)$-$220$-$ns$Rise time$t_f$-$100$-$ns$Body to drain diode forward voltageV_{DF}-1.1-VNote:3. Pulse test</th>	Gate to source breakdown voltage $V_{(BR)GSS}$ ± 30 V $I_G = \pm 100 \ \mu$ A, $V_{DS} = 0$ Gate to source leak current I_{GSS} ± 10 μ A $V_{GS} = \pm 25 \ V, V_{DS} = 0$ Zero gate voltage drain current $2SK1629$ I_{DSS} 250 μ A $V_{DS} = 360 \ V, V_{GS} = 0$ Gate to source cutoff voltage $2SK1629$ $V_{CS}(off)$ 2.0 - 3.0 V $I_D = 1 \ m$ A, $V_{DS} = 10 \ V_{DS} = 400 \ V, V_{GS} = 0$ Gate to source cutoff voltage $V_{CS}(off)$ 2.0 - 3.0 V $I_D = 1 \ m$ A, $V_{DS} = 10 \ V^3$ Static drain to source on 2SK1629 $2SK1629$ - 0.225 Ω $I_D = 15 \ A, V_{DS} = 10 \ V^3$ Forward transfer admittance $ y_{IS} $ 12 20 - S $I_D = 15 \ A, V_{DS} = 10 \ V^3$ Input capacitanceCiss- 2800 - pF $V_{DS} = 10 \ V, V_{SS} = 0$ Output capacitanceCiss- 2800 - pF $V_{DS} = 10 \ V, V_{SS} = 0$ Reverse transfer capacitanceCiss- 90 - pF I_T Turn-off delay time $t_d(off)$ - 220 - ns Rise time t_f - 100 - ns Body to drain diode forward voltage V_{DF} - 1.1 - V Note:3. Pulse test
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Gate to source leak current Isss - - ± 10 μ A V _{GS} = ± 25 V, V _{DS} = 0 Zero gate voltage drain current 2SK1628 Ibbs - - 250 μ A V _{DS} = 360 V, V _{GS} = 0 Gate to source cutoff voltage V _{SS} (df) 2.0 - 3.0 V Ib = 1 mA, V _{DS} = 10 V Static drain to source on state resistance 2SK1628 R _{DS(on)} - 0.22 0.27 Ib = 15 A, V _{GS} = 10 V Forward transfer admittance [y _{Ib}] 12 20 - S Ib = 15 A, V _{GS} = 10 V Input capacitance Ciss - 2800 - pF V _{DS} = 10 V, V _{GS} = 0, Output capacitance Ciss - 780 - pF Ib = 15 A, V _{GS} = 0, Turn-on delay time t_d(on) - 32 - ns Ib = 15 A, V _{GS} = 10 V, Rise time t_t - 140 - ns Ib = 15 A, V _{GS} = 10 V, Rise time t_t - 140 - ns Ib =
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Gate to source leak current Isss ± 10 μ A $V_{GS} = \pm 25$ V, $V_{DS} = 0$ Zero gate voltage drain current $2SK1628$ Ibbs 250 μ A $V_{DS} = 360$ V, $V_{GS} = 0$ Gate to source cutoff voltage $2SK1628$ $2SK1628$ 2.0 3.0 V $b = 1$ mA, $V_{DS} = 10$ V State drain to source on state resistance $2SK1628$ $R_{DS(on)}$ 0.22 0.27 $b = 15$ A, $V_{GS} = 10$ V Forward transfer admittance $[y_{1s}]$ 12 20 S $b = 15$ A, $V_{GS} = 10$ V, $V_{GS} = 0$ Input capacitance Ciss 2800 pF $V_{DS} = 10$ V, $V_{GS} = 0$, Output capacitance Ciss 780 pF $f = 1$ MHz Reverse transfer capacitance Crss 90 pF Turn-on delay time t_t 140 ns $b = 15$ A, $V_{GS} = 10$ V, Rise time t_t 140
current2SK1629VGS(off)2.0-3.0VIp = 1 mA, Vps = 10 VGate to source cutoff voltageVGS(off)2.0-3.0VIp = 1 mA, Vps = 10 VStatic drain to source on state resistance2SK1628 2SK1629RpS(on)-0.200.25 Ω Ip = 15 A, Vgs = 10 VForward transfer admittance19/ts1220-SIp = 15 A, Vps = 10 V***Forward transfer admittance19/ts1220-SIp = 15 A, Vps = 10 V***Input capacitanceCiss-2800-pFVps = 10 V, Vgs = 0,***Output capacitanceCoss-780-pFf = 1 MHzReverse transfer capacitanceCrss-90-pFf = 1 MHzTurn-on delay timetd(off)-322-nsIp = 15 A, Vgs = 10 V,Rise timetr-140-nsRs = 2 \OmegaTurn-off delay timetd(off)-200-nsRs = 2 \OmegaFall timetr-100-nsIF = 30 A, Vgs = 0,Body to drain diode forward voltageVpF-1.1-VIF = 30 A, Vgs = 0,Body to drain diode reverse recoverytrr-600-nsIF = 30 A, Vgs = 0,di draindidde reverse recoverytrr-600-nsIF = 30 A, Vgs = 0,	current 2SK1629 V _{GS} = 0 V _{DS} = 400 V, V _{GS} = 0 Gate to source cutoff voltage V _{GS} (off) 2.0 - 3.0 V I _D = 1 mA, V _{DS} = 10 V Static drain to source on state resistance 2SK1628 2SK1629 R _{DS(on)} - 0.20 0.25 Ω I _D = 1 mA, V _{DS} = 10 V Forward transfer admittance [Jyts] 12 20 - S I _D = 15 A, V _{DS} = 10 V * ³ Input capacitance Ciss - 2800 - pF V _{DS} = 10 V, V _{GS} = 0, Output capacitance Ciss - 2800 - pF V _{DS} = 10 V, V _{GS} = 0, Output capacitance Ciss - 2800 - pF V _{DS} = 10 V, V _{GS} = 0, Reverse transfer capacitance Crss - 90 - pF Turn-on delay time t _{d(off)} - 32 - ns I _D = 15 Å, V _{GS} = 10 V, Turn-off delay time t ₁ - 140 - ns I _P = 30 Å, V _{GS} = 0
Gate to source cutoff voltageVGS(off)2.0-3.0VIbe 1 mA, VDS = 10 VStatic drain to source on state resistance $2SK1628$ $2SK1629$ $R_{DS(on)}$ -0.200.25 $ \Omega$ Ib = 15 A, VGS = 10 V *3Forward transfer admittance $2SK1629$ $-$ 0.220.27 Ω Ib = 15 A, VGS = 10 V *3Input capacitanceCiss-2800-pFVDS = 10 V, VGS = 0,Output capacitanceCoss-780-pFVDS = 10 V, VGS = 0,Output capacitanceCrss-90-pFf = 1 MHzReverse transfer capacitanceCrss-90-pFTurn-on delay timetd(on)-32-nsIb = 15 A, VGS = 10 V,Rise timetr-140-nsRL = 2 Ω Turn-off delay timetd(off)-200-nsRL = 2 Ω Fall timetr-100-nsIF = 30 A, VGS = 0Body to drain diode forward voltageVDF-1.1-VIF = 30 A, VGS = 0,Body to drain diode reverse recoverytrr-600-nsIF = 30 A, VGS = 0,It makestrr-600-nsIF = 30 A, VGS = 0,IF = 30 A, VGS = 0,	Gate to source cutoff voltageVGS(off)2.0-3.0VIb = 1 mA, VDS = 10 VStatic drain to source on state resistance2SK1628RDS(on)-0.200.25 Ω Ib = 15 A, VDS = 10 VForward transfer admittance[yts]1220-SIb = 15 A, VDS = 10 V *3 Input capacitanceCiss-2800-pFVDS = 10 V, VdS = 0, VDS = 10 V, VdS = 0, VDS = 10 V, VdS = 0, VDS = 10 V, Vd
Static drain to source on state resistance $2SK1628$ $R_{DS(on)}$ 0.20 0.25 Ω $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$ Forward transfer admittance $ y_{fs} $ 12 20 S $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$ Input capacitance Ciss 2800 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitance Coss 780 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Reverse transfer capacitance Crss 90 pF Turn-on delay time $t_{d(on)}$ 32 ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise time t_r 140 pF $I_{P} = 15 \text{ A},$ $V_{GS} = 10 \text{ V},$ Rise time t_r 140 ns $I_D = 15 \text{ A},$ $V_{GS} = 10 \text{ V},$ Fall time t_r 140 ns $I_F = 30 \text{ A},$ $V_{GS} = 0$ Body to drain diode forward voltage V_{DF} 1.1 V $I_F = 30 \text{ A},$	Static drain to source on state resistance $2SK1628$ $2SK1629$ $R_{DS(on)}$ -0.200.25 Ω $I_{D} = 15 \text{ A}, V_{GS} = 10 \text{ V}^{+3}$ Forward transfer admittance $ y_{fs} $ 1220-S $I_{D} = 15 \text{ A}, V_{DS} = 10 \text{ V}^{+3}$ Input capacitanceCiss-2800-pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitanceCoss-780-pFReverse transfer capacitanceCrss-90-pFTurn-on delay time $t_{d(on)}$ -32-nsTurn-off delay time $t_{d(off)}$ -200-nsFall timeti-100-nsBody to drain diode forward voltage V_{DF} -1.1-VNote:3. Pulse test
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Forward transfer admittance $ y_{fs} $ 1220S $I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$ Input capacitanceCiss2800pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitanceCoss780pF $f = 1 \text{ MHz}$ Reverse transfer capacitanceCrss90pFTurn-on delay time $t_{d(on)}$ 32ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise timetr140ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Turn-off delay time $t_{d(off)}$ 200nsFall timetr100nsBody to drain diode forward voltage V_{DF} 1.1VBody to drain diode reverse recovery t_{rr} 600nsImage V_{Tr} 600nsI_F = 30 \text{ A}, V_{GS} = 0, di (4t - 100 \text{ A}) u_D	Forward transfer admittance $ y_{fs} $ 1220S $ _{D} = 15 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$ Input capacitanceCiss2800pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitanceCoss780pFReverse transfer capacitanceCrss90pFTurn-on delay time $t_{d(on)}$ 32nsRise timetr140nsTurn-off delay time $t_{d(off)}$ 200nsFall timetr100nsBody to drain diode forward voltage V_{DF} 1.1VNote:3. Pulse test
Input capacitanceCiss-2800-pF $V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0,$ Output capacitanceCoss-780-pFf = 1 MHzReverse transfer capacitanceCrss-90-pFTurn-on delay time $t_{d(on)}$ -32-nsIp = 15 Å, V_{GS} = 10 V,Rise timetr-140-nsRL = 2 Ω Turn-off delay time $t_{d(off)}$ -200-nsFall timetr-100-nsBody to drain diode forward voltage V_{DF} -1.1-VBody to drain diode reverse recovery t_{rr} -600-nsIr = 30 Å, $V_{GS} = 0,$ time100 Å Viga	Input capacitanceCiss-2800-pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitanceCoss-780-pFf = 1 MHzReverse transfer capacitanceCrss-90-pFTurn-on delay time $t_{d(on)}$ -32-ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise timetr-140-ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Turn-off delay time $t_d(on)$ -200-nsFall timetr-100-nsBody to drain diode forward voltage V_{DF} -1.1-VBody to drain diode reverse recovery timetrr-600-nsNote:3. Pulse test-100 A/µs-100 A/µs
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Reverse transfer capacitanceCrss90pFTurn-on delay time $t_{d(on)}$ 32nsI_b = 15 A, V_{GS} = 10 V,Rise time t_r 140nsR_L = 2 Ω Turn-off delay time $t_{d(off)}$ 200nsFall time t_f 100nsBody to drain diode forward voltage V_{DF} 1.1VBody to drain diode reverse recovery t_{rr} 600nsIr = 30 A, V_{GS} = 0,nsI_F = 30 A, V_{GS} = 0,time t_{rr} 600nsI_F = 30 A, V_{GS} = 0,	Reverse transfer capacitanceCrss90 pF Turn-on delay time $t_{d(on)}$ 32ns $l_0 = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise time t_r 140ns $R_L = 2 \Omega$ Turn-off delay time $t_{d(off)}$ 200nsFall time t_f 100nsBody to drain diode forward voltage V_{DF} 1.1VBody to drain diode reverse recovery t_{rr} 600nsImage: Note:3. Pulse testImage: Note:3. Pulse testImage: Note:Image: Note:
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Turn-on delay time $t_{d(on)}$ 32nsIb = 15 A, V_{GS} = 10 V,Rise time t_r 140nsRL = 2 Ω Turn-off delay time $t_{d(off)}$ 200nsFall time t_r 100nsBody to drain diode forward voltage V_{DF} 1.1VBody to drain diode reverse recovery t_{rr} 600nsIn timeNote:3. Pulse test1.1V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Turn-on delay time $t_{d(on)}$ 32nsIb = 15 A, V_{GS} = 10 V,Rise time t_r 140nsRL = 2 Ω Turn-off delay time $t_{d(off)}$ 200nsFall time t_r 100nsBody to drain diode forward voltage V_{DF} 1.1VBody to drain diode reverse recovery t_{rr} 600nsIn timeNote:3. Pulse test1.1V
Rise time t_r -140-ns $R_L = 2 \Omega$ Turn-off delay time $t_{d(off)}$ -200-nsFall time t_f -100-nsBody to drain diode forward voltage V_{DF} -1.1-VBody to drain diode reverse recovery t_{rr} -600-nsIF = 30 A, V _{GS} = 0,1.1-V	Rise timetr-140-nsRL = 2 Ω Turn-off delay timetd(off)-200-nsFall timetr-100-nsBody to drain diode forward voltageVDF-1.1-VBody to drain diode reverse recoverytrr-600-nsIre = 30 A, VGS = 0, dir/dt = 100 A/µsNote:3. Pulse test
Turn-off delay time $t_{d(off)}$ 200nsFall time t_f 100nsBody to drain diode forward voltage V_{DF} 1.1VBody to drain diode reverse recovery t_{rr} 600nsIF = 30 A, V _{GS} = 0,Body to drain diode reverse recovery t_{rr} 600ns	Turn-off delay time $t_{d(off)}$ 200nsFall time t_f 100nsBody to drain diode forward voltage V_{DF} 1.1VBody to drain diode reverse recovery t_{rr} 600nsIF = 30 A, V_{GS} = 0, timeNote:3. Pulse test
Fall time t_f -100-nsBody to drain diode forward voltage V_{DF} -1.1-VIF = 30 A, V_{GS} = 0Body to drain diode reverse recovery t_{rr} -600-nsIF = 30 A, V_{GS} = 0,time	Fall time t_f -100-nsBody to drain diode forward voltage V_{DF} -1.1-V $I_F = 30 \text{ A}, V_{GS} = 0$ Body to drain diode reverse recovery t_{rr} -600-ns $I_F = 30 \text{ A}, V_{GS} = 0,$ timeNote:3. Pulse test
Body to drain diode forward voltage V_{DF} -1.1- V $I_F = 30 \text{ A}, V_{GS} = 0$ Body to drain diode reverse recovery t_{rr} -600-ns $I_F = 30 \text{ A}, V_{GS} = 0$ time	Body to drain diode forward voltage V _{DF} - 1.1 - V I _F = 30 A, V _{GS} = 0 Body to drain diode reverse recovery time trr - 600 ns I _F = 30 A, V _{GS} = 0, di _F /dt = 100 A/µs Note: 3. Pulse test
Body to drain diode reverse recovery t_{rr} — 600 \leftarrow ns $I_F = 30 \text{ A}, V_{GS} = 0,$	Body to drain diode reverse recovery t_{rr} — 600 — ns $I_F = 30 \text{ A}, V_{GS} = 0, di_F/dt = 100 \text{ A}/\mu \text{s}$ Note: 3. Pulse test
	time di _F /dt = 100 A/μs
Note: 3. Pulse test	Note: 3. Pulse test
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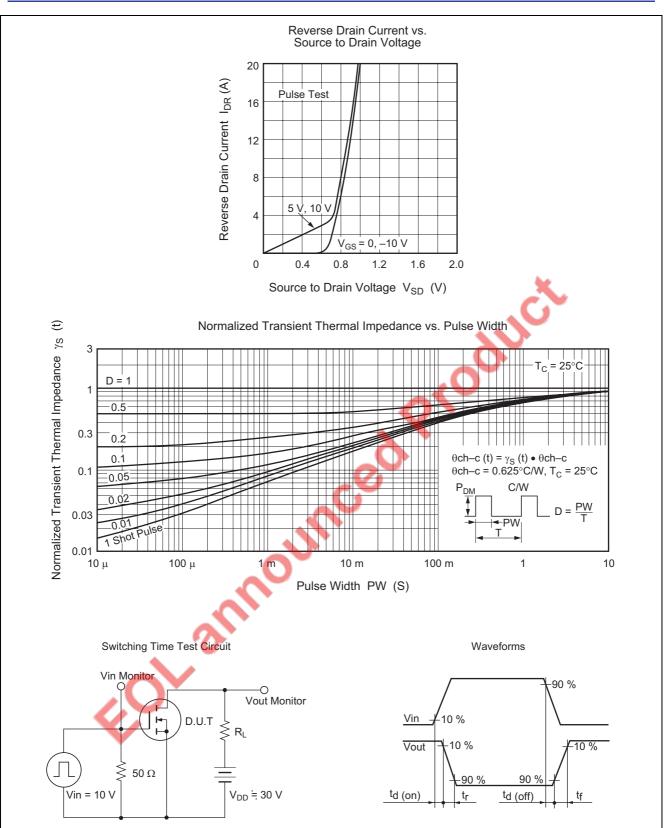
Main Characteristics



RENESAS

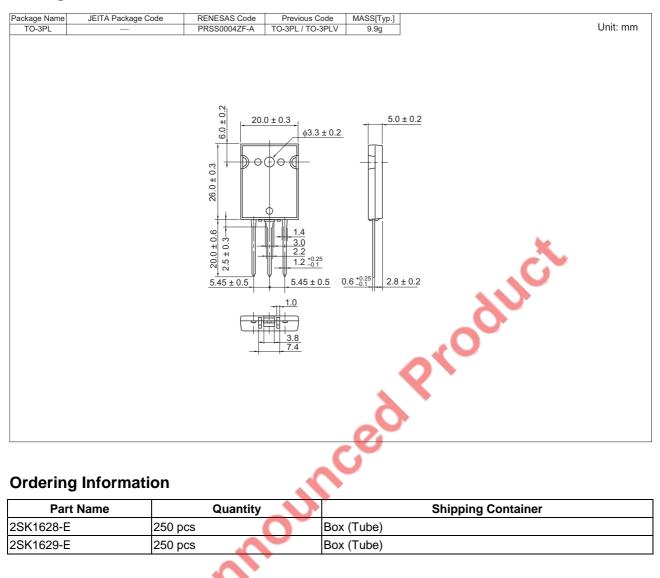


RENESAS



RENESAS

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1628-E	250 pcs	Box (Tube)
2SK1629-E	250 pcs	Box (Tube)
	or sur	

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